

Low-power voltage repeater with $\pm 0,5$ % accuracy with low drop voltage

(FUNCTIONAL EQUIVALENT OF TLE4250 INFINEON)

ILE4250G, ILE4250S - are integrated circuits of low-power voltage repeater (adapter) with $\pm 0,5$ % accuracy, load capacity up to 50 mA and with low-drop voltage. ICs realized in 5-pin plastic packages ILE4250G - P-TO263-5-1, ILE4250S – P-TO220-5-12.

Integrated circuits of low-power voltage repeater (adapter) are purposed to transfer voltage with $\pm 0,5$ % accuracy (for load current 1...50mA) at a range of input voltages from 6 to 28 V, with $\pm 0,5$ % accuracy (for load current 1...10mA) at a range of input voltages from 6 to 40 V, and with $\pm 0,1$ % accuracy (for load current 1...10mA) at a range of input voltages from 6 to 16 V.

Drop voltage is less 0,3 at load current 10 mA. The ICs are tolerant to over voltage of both polarities (positive & negative). Adjustment pin input voltage ICs is in range from 2 to 36 V

The ICs are used in power supply units of electronic devices, especially in automotive electronics.

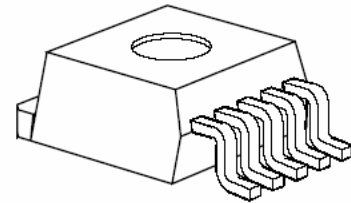


Fig. 1 – View of IC in P-TO263-5-1 package

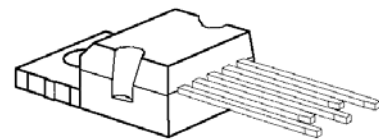


Fig. 2 – View of IC in P-TO220-5-12 package

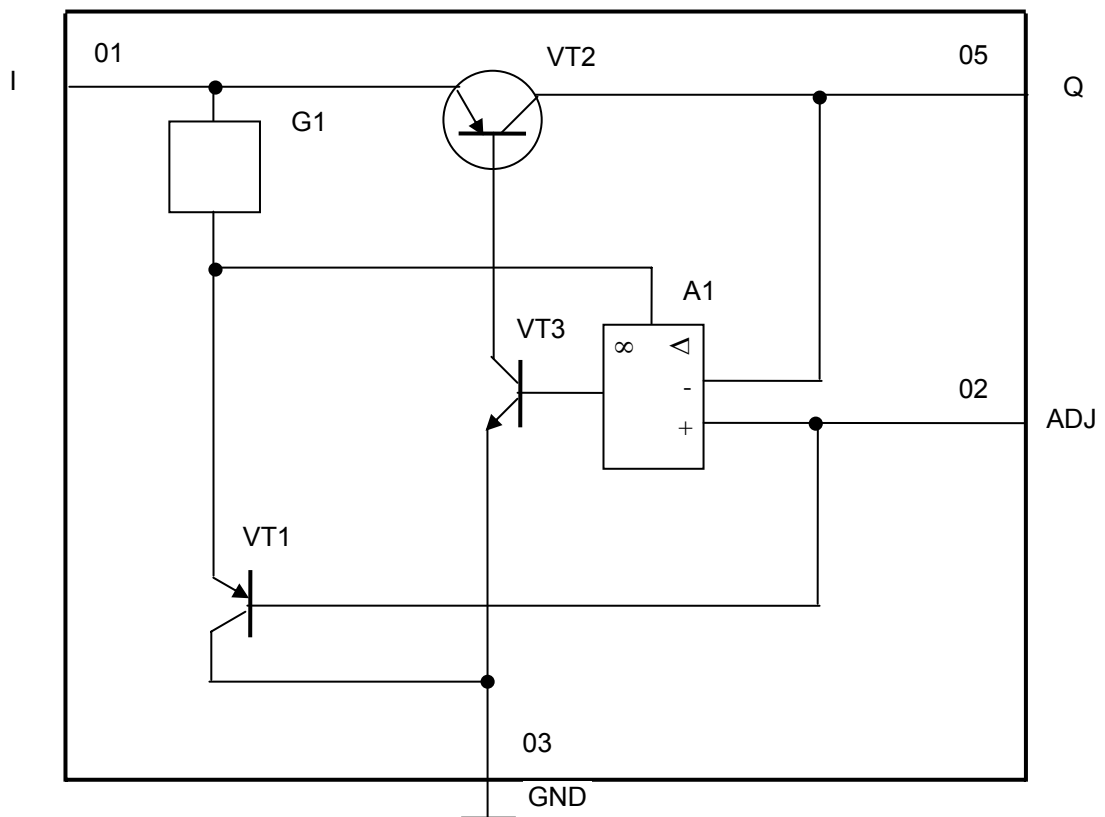
Main features

- High accuracy of the output voltage $\pm 0,5\%$;
- Low-drop voltage ;
- Built in overheating protection;
- Reverse polarity proof;
- Low consumption current;
- Input voltage from 3 to 40 V;
- Suitable for use in automotive electronics;
- Wide junction temperature range -40 ... +150°C;

Permissible value of ESD potential 1000V

Table 1 Pins description

| Package pin number | Chip pad number | Symbol | Function |
|--------------------|-----------------|--------|--------------------------|
| 01 | 01 | I | Input |
| 02 | 02 | ADJ | Adjustment/disable input |
| 03 | 03 | GND | Common pin (Ground) |
| 04 | - | NC | Not connected pin |
| 05 | 04 | Q | Output |



A1 –amplifier;
 G1 – current source;
 VT1 – VT3 - transistors

Fig. 3 – Electric block diagram

Table 2 Absolute Maximum Ratings

| Symbol | Parameters | Norm | | Unit |
|------------------|--------------------------------|--------|------|------|
| | | min. | max. | |
| T _J | Junction temperature | -40* | 150 | °C |
| T _{stg} | Storage temperature | -50 | 150 | °C |
| U _I | Input voltage | -42 | 45 | V |
| U _Q | Output voltage | -1** | 40** | V |
| U _{ADJ} | Adjustment/disable pin voltage | -0,3** | 40** | |

* Ambient temperature is indicated.
 ** Voltage is not applied to input I

Table 3 – Recommended operation modes

| Symbol | Parameter | Norm | | Unit |
|------------------|--------------------------------|------|------|------|
| | | Min. | Max. | |
| T _J | Junction temperature | -40* | 150 | °C |
| U _I | Input voltage | 3 | 40 | V |
| U _{ADJ} | Adjustment/disable pin voltage | 2 | 36 | V |

Note:

Maximum power P_{tot}, W, dissipated by IC at ambient temperature T_A, is calculated by formula:

$$P_{tot} = (150 - T_A) / R_{th\ j-a} , \quad (1)$$

150 – maximum permissible operating junction temperature, °C.

R_{th j-a} - thermal resistance junction ambient, °C /W,

for ILE4250G without heat sink R_{th ja} is equal 80 °C /W

for ILE4250S without heat sink R_{th ja} is equal 65 °C /W

for IC with heat sink R_{th ja} is calculated by formula

$$R_{th\ j-a} = R_{th\ j-c} + R_{th\ c-a} , \quad (2)$$

R_{th j-c} - thermal resistance junction case, °C /W. R_{th jc} = 4 °C/W.

Thermal resistance case-ambient R_{th c-a} is determined by heat sink design and is selected by IC customer.

Application circuit and heat sink and ambient temperature have to provide junction temperature not more T_J ≤ 150 °C.

* Ambient temperature is indicated.

Table 4 – Electric parameters

($U_I = 13,5 \text{ V}$, $U_{ADJ} > 2,0 \text{ V}$, $-40 \text{ °C} \leq T_J \leq 150 \text{ °C}$ unless otherwise specified)

| Symbol | Parameter | Mode of measurement | Norm | | Unit |
|---|---|---|-------|------|------|
| | | | Min. | Max. | |
| ΔU_Q | Voltage repeating accuracy | $6 \text{ V} \leq U_I \leq 28 \text{ V}$ $-1 \text{ mA} \leq I_Q \leq -50 \text{ mA}$ | - 0,5 | 0,5 | % |
| | | $6 \text{ V} \leq U_I \leq 40 \text{ V}$ $-1 \text{ mA} \leq I_Q \leq -10 \text{ mA}$ | - 0,5 | 0,5 | |
| | | $6 \text{ V} \leq U_I \leq 16 \text{ V}$ $-1 \text{ mA} \leq I_Q \leq -10 \text{ mA}$ | - 0,1 | 0,1 | |
| U_{dr} | Drop voltage | $I_Q = -10 \text{ mA}$, $U_{ADJ} > 4.0 \text{ V}$ Note 2 | - | 0,3 | V |
| I_q | Consumption current $I_q = I_I - I_Q$ | $I_Q \leq -30 \text{ mA}$ | - | 3,0 | mA |
| | | $I_Q \leq -1 \text{ mA}$ | - | 0,15 | |
| | | $U_{ADJ} = 0 \text{ V}$, $T_J < 85 \text{ °C}$ | - | 0,02 | |
| | | $U_{ADJ} = U_I = 5 \text{ V}$, $I_Q = 0 \text{ mA}$ | - | 3,0 | |
| I_{Qmax} | Maximum output current | $T_J \leq 125 \text{ °C}$ Note 2 | 50 | - | mA |
| $\Delta U_{Q(U)}$ | Supply (input) voltage regulation of output voltage | $6 \text{ V} \leq U_I \leq 40 \text{ V}$ $I_Q = -10 \text{ mA}$ | -10 | 10 | mV |
| $\Delta U_{Q(I)}$ | Load current regulation of output voltage | $-1 \text{ mA} \leq I_Q \leq -30 \text{ mA}$ | - 15 | 15 | mV |
| Adjustment/disable input parameters | | | | | |
| I_{ADJ} | Adjustment/disable pin current | $U_{ADJ} = 5 \text{ V}$ $T_J < 125 \text{ °C}$ | - | 0,5 | mA |
| $U_{ADJ \text{ off}}$ | Adjustment /disable pin switching off voltage | IC is off $T_J < 125 \text{ °C}$ | 0,8 | - | V |
| U_{ADJ} | Adjustment range | $ U_Q - U_{ADJ} < 0,5\%$, $U_I \geq U_Q + 0,3 \text{ V}$, $T_J < 125 \text{ °C}$ | 2,0 | 36 | V |
| <p>Notes</p> <p>1. Measurement of electric parameters is processed with connected input capacities $C_{I1} = 100 \mu\text{F}$, and output capacity $C_Q = 2,2 \mu\text{F}$.</p> <p>2. Parameter is measured, when the output voltage V_Q has dropped 100 mV from the nominal value obtained at $U_I = 13.5 \text{ V}$.</p> <p>_____</p> <p>* Ambient temperature is indicated.</p> | | | | | |



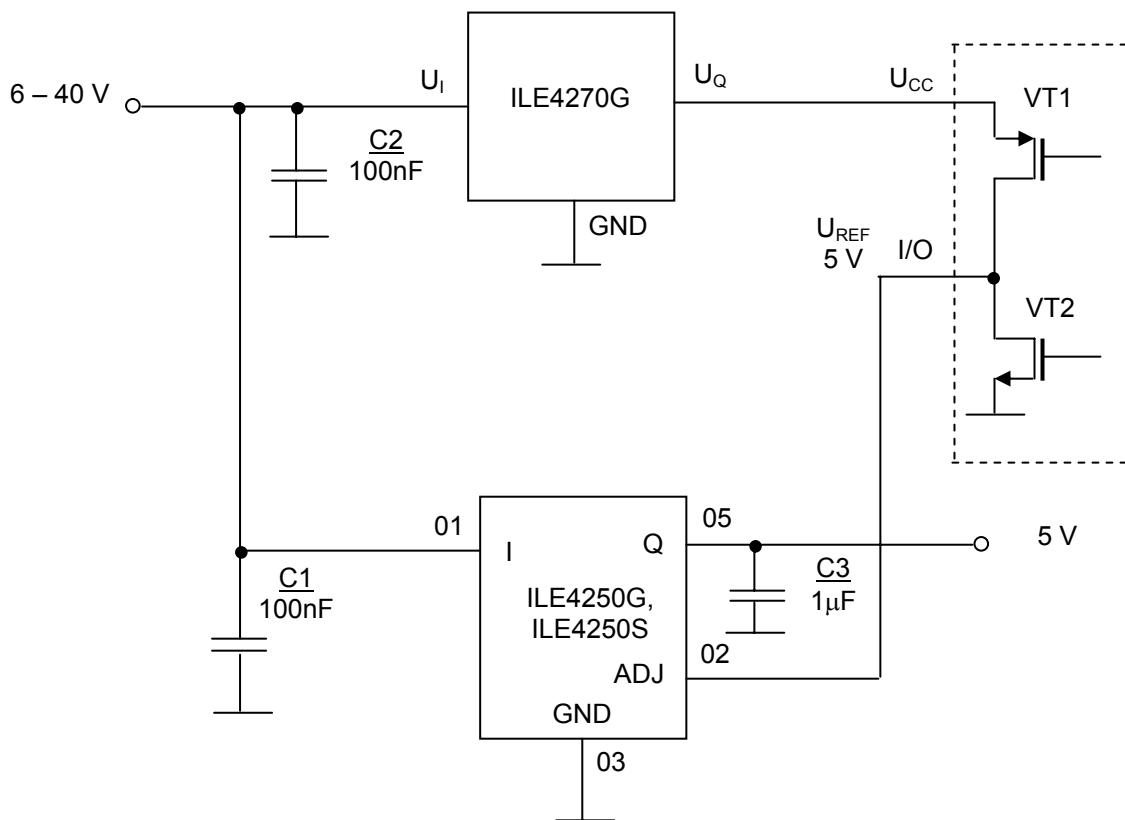
Table 5 – Typical electric parameters

($U_I = 13,5\text{ V}$, $U_{ADJ} > 2,0\text{ V}$, $-40\text{ °C} \leq T_J \leq 150\text{ °C}$ unless otherwise specified)

| Symbol | Parameter | Mode of measurement | Typical value | Unit |
|--------|------------------------|---|---------------|------|
| PSRR | Ripple rejection ratio | $f_r = 100\text{ Hz}$, $I_Q = -100\text{ mA}$ $U_r = 0,5^{**}\text{ V (p - p)}$ | 60 | dB |

* Ambient temperature is indicated.

** It is permitted to measure at $U_{r(p-p)} = 3\text{ V}$, but for that PSRR norm to be revised



VT1, VT2 – transistors

Fig 4 – Typical application diagram

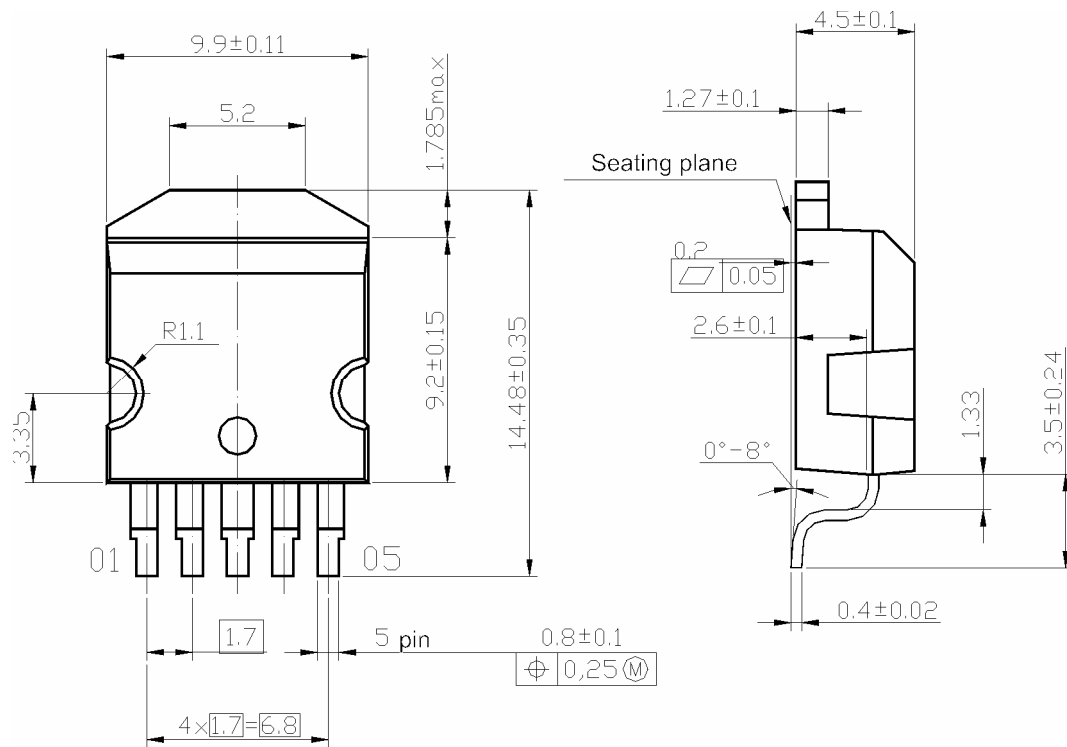


Fig 5 – P-TO263-5-1 package outline

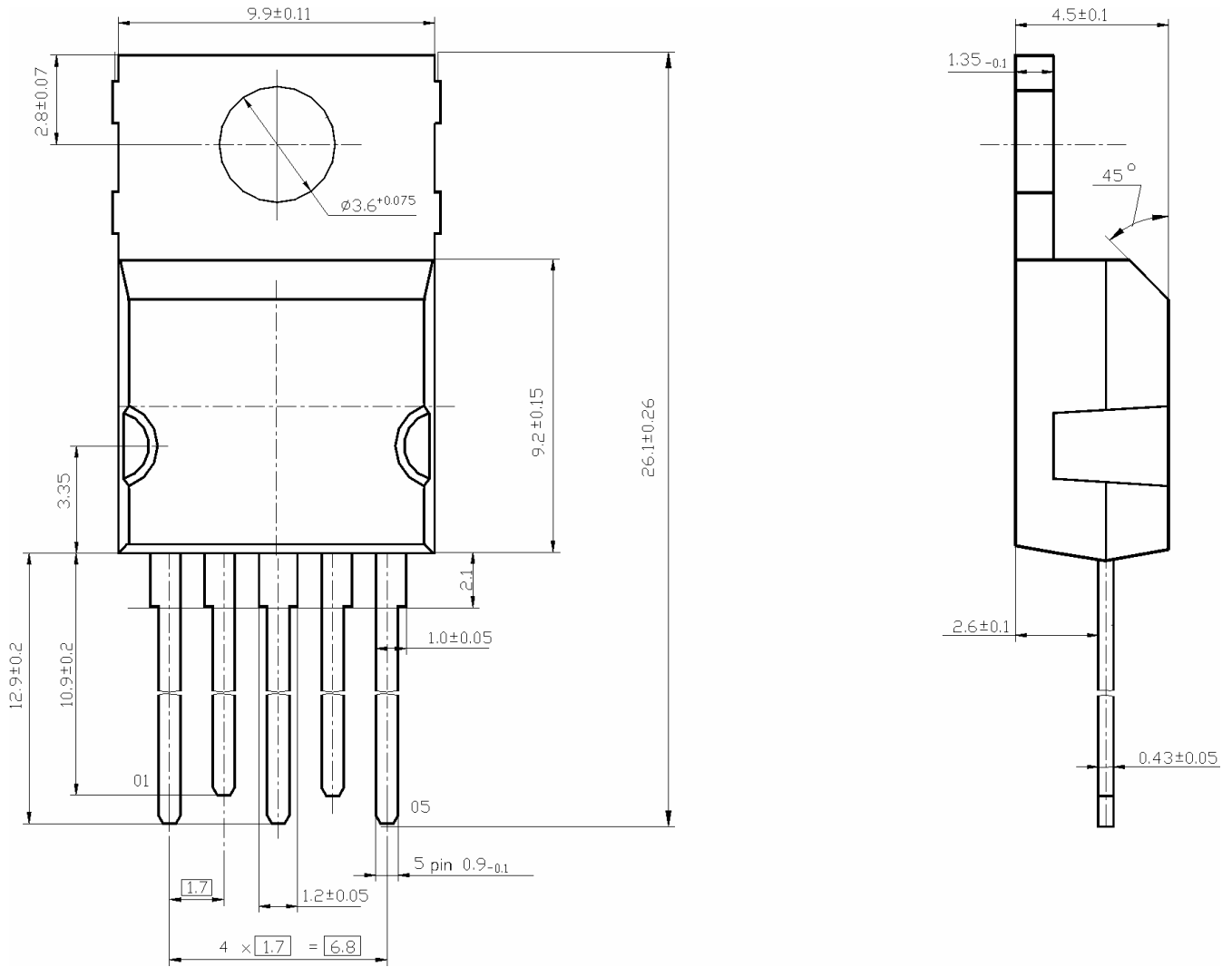
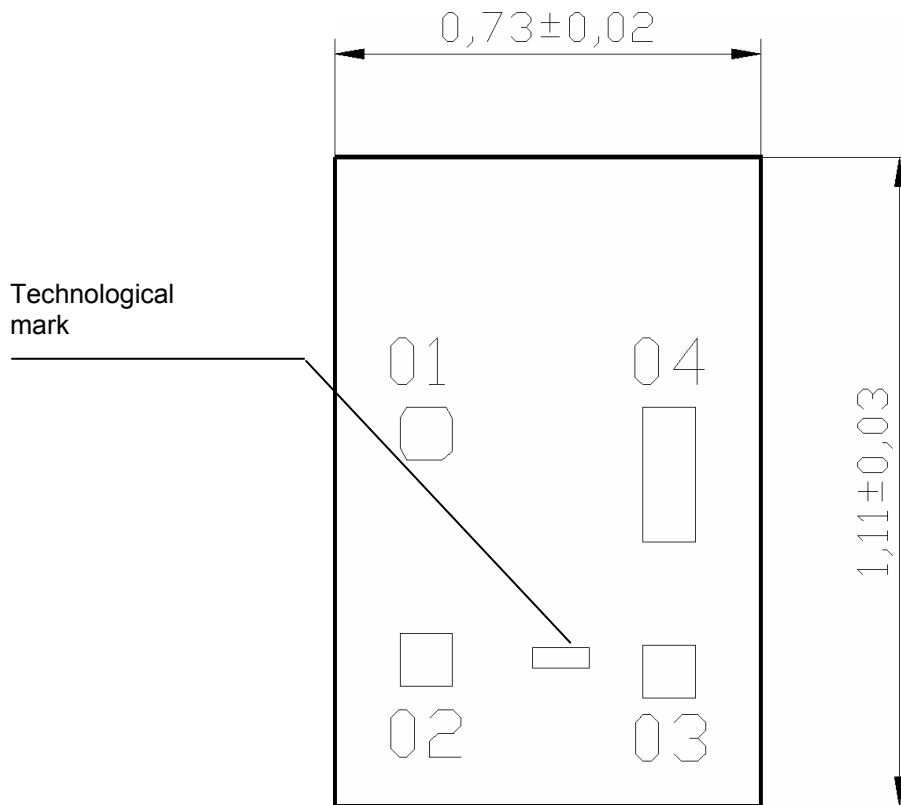


Fig. 6 – P-TO220-5-12 package outline



Contact pad coordinates are indicated in the table 6.

Technological mark on chip «4250.» has coordinates, mm: left bottom corner $x = 0,340$, $y = 0,210$.

Chip thickness is $0,35 \pm 0,02$.

Fig. 7– Chip outline drawing

Table 6 Contact pad location table

| Contact pad number | Coordinates (Left bottom corner), mm | |
|--------------------|--------------------------------------|-------|
| | X | Y |
| 01 | 0,112 | 0,593 |
| 02 | 0,112 | 0,206 |
| 03 | 0,528 | 0,186 |
| 04 | 0,528 | 0,453 |

Notes

- Coordinates and size of the contact pads are given by the layer «Passivation»
- Sizes of contact pads are
pads 01-03 - 0,090 x 0,090 mm,
pad 04 - 0,090 x 0,230 mm.
- Bevel of two corners of the first contact pad (24 ± 2) μm